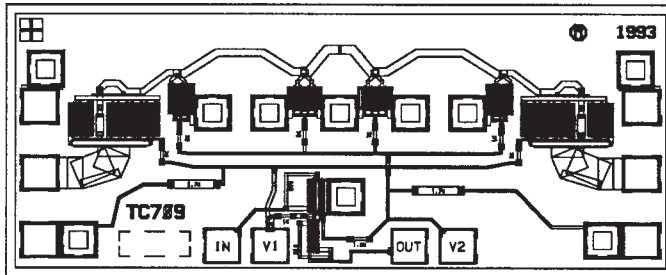




Agilent HMMC-1015 DC–50 GHz Variable Attenuator Data Sheet



Chip Size: 1470 x 610 μm (57.9 x 24.0 mils)
 Chip Size Tolerance: $\pm 10 \mu\text{m}$ (± 0.4 mils)
 Chip Thickness: $127 \pm 15 \mu\text{m}$ (5.0 ± 0.6 mils)

Features

- **Specified Frequency Range:**
DC–26.5 GHz
- **P_{in} (-1dB):**
27 dBm @ 500 MHz
- **Return Loss:**
10 dB
- **Minimum Attenuation:**
2.0 dB
- **Maximum Attenuation:**
30.0 dB

Description

The HMMC-1015 is a monolithic, voltage variable, GaAs IC attenuator that operates from DC to 50 GHz. The distributed topology of the HMMC-1015 minimizes the parasitic effects of its series and shunt FETs, allowing the HMMC-1015 to exhibit a wide dynamic range across its full bandwidth. An on-chip DC reference circuit may be used to maintain optimum VSWR for any attenuation setting or to improve the attenuation versus voltage linearity of the attenuator circuit.

Absolute Maximum Ratings^[1]

Symbol	Parameters/Conditions	Units	Min.	Max.
V_{DC-RF}	DC Voltage to RF Ports	V	-0.6	+1.6
V_1	V_1 Control Voltage	V	-10.5	+0.5
V_2	V_2 Control Voltage	V	-10.5	+0.5
V_{DC}	DC In/DC Out	V	-0.6	+1.0
P_{IN}	RF Input Power	dBm		17
T_{mina}	Min. Ambient Operating Temp.	$^{\circ}\text{C}$	-55	
T_{maxa}	Max. Ambient Operating Temp.	$^{\circ}\text{C}$		+125
T_{stg}	Storage Temperature	$^{\circ}\text{C}$	-65	+165
T_{max}	Max. Assembly Temp. (for 60 sec. max.)	$^{\circ}\text{C}$		+300

Note:

1. Operation in excess of any one of these conditions may result in damage to this device.



Agilent Technologies

HMMC-1015 DC Specifications/Physical Properties, $T_A = 25^\circ\text{C}$

Symbol	Parameters and Test Conditions	Units	Min.	Typ.	Max.
I_{V1}	V_1 Control Current, ($V_1 = -10\text{V}$)	mA	5.0	5.9	7.1
I_{V2}	V_2 Control Current, ($V_2 = -10\text{V}$)	mA	5.0	5.9	7.1
V_P	Pinch-Off Voltage	V	-6.75	-5.0	-3.75

Electrical Specifications^[1], $T_A = 25^\circ\text{C}$, $Z_0 = 50\Omega$

Parameters and Test Conditions	Units	Freq. (GHz)	Min.	Typ.	Max.
Minimum Attenuation, $ S_{21} $ ($V_1 = 0\text{ V}$, $V_2 = -10\text{ V}$)	dB	1.5		1.0	2.4
		8.0		1.4	2.4
		20.00		1.7	2.4
		26.5		2.0	2.4
		50.0		3.9	
Input/Output Return Loss @ Min. Attenuation Setting, ($V_1 = 0\text{ V}$, $V_2 = -10\text{ V}$)	dB	<26.5	10	16	
		<50.0		8	
Maximum Attenuation, $ S_{21} $ ($V_1 = -10\text{ V}$, $V_2 = 0\text{ V}$)	dB	1.5	27	30	
		8.0	27	38	
		20.0	27	38	
		26.5	27	40	
		50.0		35	
$P_{-1\text{dB}}$ @ Minimum Attenuation	dBm	300 kHz		18.5	
	dBm	>500 MHz		27	
Input/Output Return Loss @ Max. Attenuation Setting, ($V_1 = -10\text{ V}$, $V_2 = 0\text{ V}$)	dB	<26.5	8	10	
	dB	<50.0		10	
DC Power Dissipation, $V_1 = -10.5\text{ V}$, $V_2 = -10.5\text{ V}$ (does not include input signals)	mW				158

Note:

1. Attenuation is a positive number; whereas, S_{21} as measured on a Network Analyzer would be a negative number.

Application

The HMMC-1015 is designed to be used as a gain control block in an ALC assembly. Because of its wide dynamic range and return loss performance, the HMMC-1015 may also be used as a broadband pulse modulator or single-pole single-throw, non-reflective switch.

Operation

The attenuation value of the HMMC-1002 is adjusted by applying negative voltage to V_2 . At any attenuation setting, optimum VSWR is obtained by applying negative voltage to V_1 . Applying negative voltage (V_2) to the gates of the shunt FETs sets the source-to-drain resistance and establishes the attenuation level. Applying negative voltage (V_1) to the gates of the series FETs optimizes the input and output match for different attenuation settings. In some applications, a single setting of V_1 may provide

sufficient input and output match over the desired attenuation range (V_2). For any HMMC-1015 the values of V_1 may be adjusted so that the device attenuation versus voltage is monotonic for both V_1 and V_2 ; however, this will slightly degrade the input and output return loss.

The attenuation and input/output match of the HMMC-1015 may also be controlled using only a single input voltage by utilizing the on-chip DC reference circuit and the driver circuit shown in Figure 4. This circuit optimizes VSWR for any attenuation setting. Because of process variations, the values of V_{REF} , R_{REF} , and R_L are different for each wafer if optimum performance is required. Typical values for these elements are given. The ratio of the resistors R_1 and R_2 determines the sensitivity of the attenuation versus voltage

performance of the attenuator. For more information on the performance of the HMMC-1015 and the driver circuits previously mentioned see MWTC's Application Note #37, "HMMC-1021 Attenuator: Attenuation Control." For more S-parameter information, see MWTC's Application Note #44, "HMMC-1015 Attenuator: S-Parameters."

Assembly Techniques

GaAs MMICs are ESD sensitive. ESD preventive measures must be employed in all aspects of storage, handling, and assembly. MMIC ESD precautions, handling considerations, die attach and bonding methods are critical factors in successful GaAs MMIC performance and reliability. Agilent application note #54, "GaAs MMIC ESD, Die Attach and Bonding Guidelines" provides basic information on these subjects.

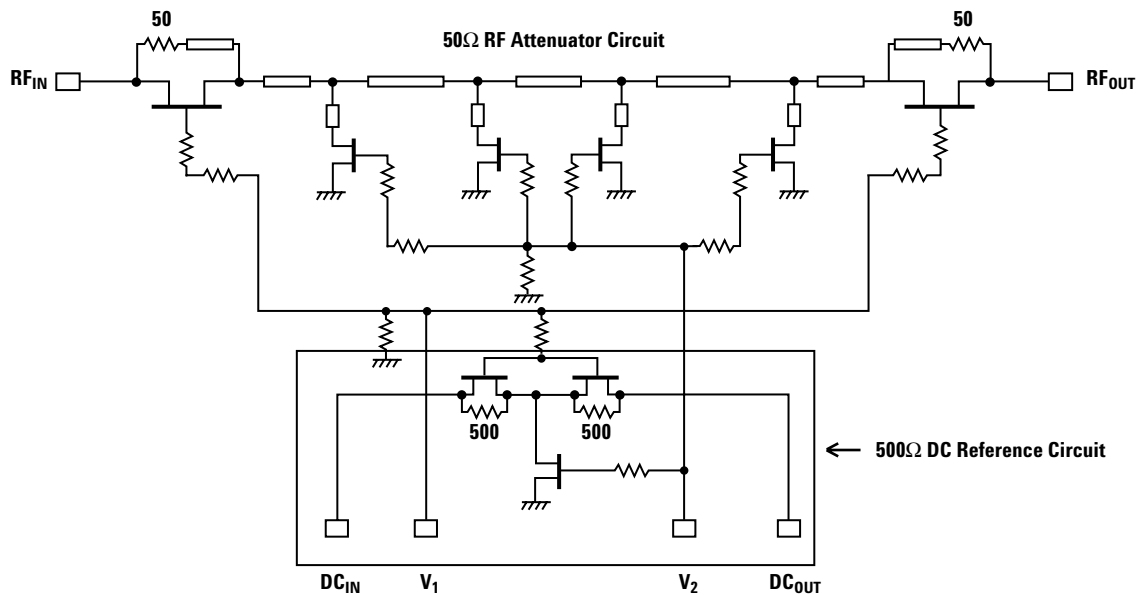
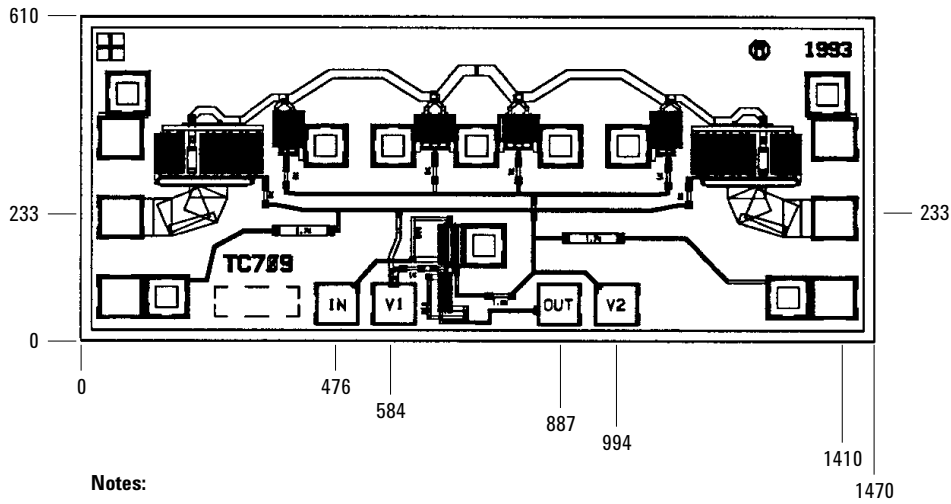


Figure 1. HMMC-1015 Schematic.



Notes:

1. All dimensions in microns and shown to center of bond pad.
2. DC_{in} , V_1 , DC_{out} , and V_2 bonding pads are 75×75 microns.
3. RF input and output bonding pads are 60×70 microns.
4. Chip thickness: $127 \pm 15 \mu\text{m}$.

Figure 2. HMMC-1015 Bonding Pad Locations.

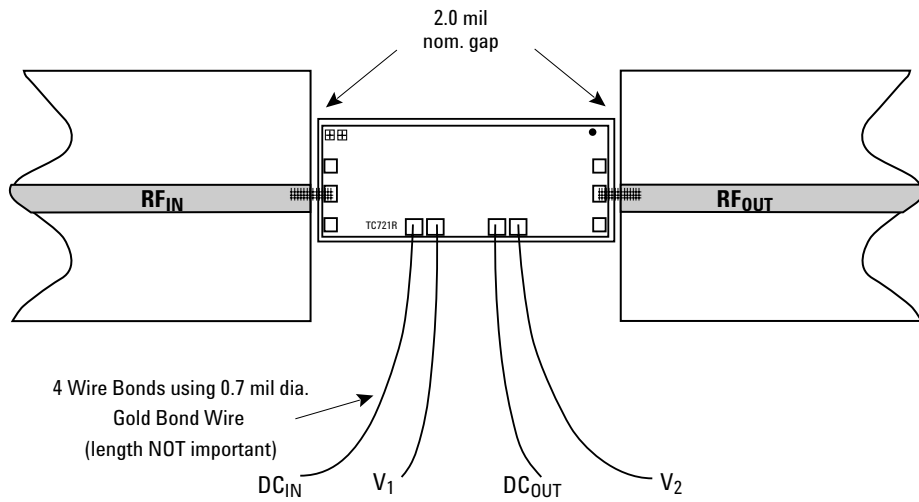


Figure 3. HMMC-1015 Assembly Diagram.

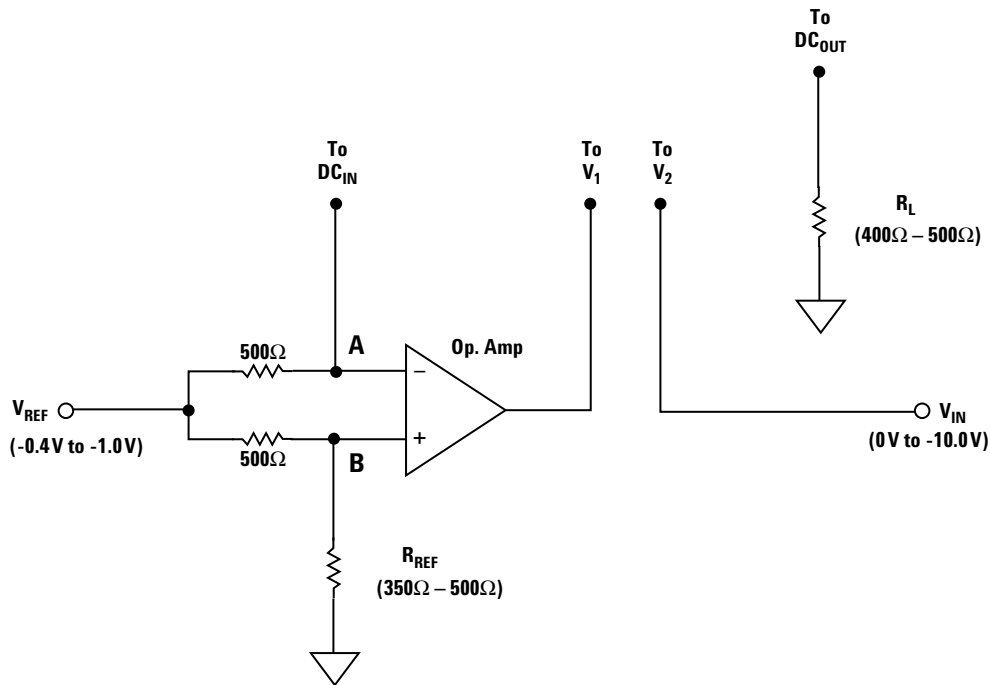


Figure 4. Attenuator Driver.

HMMC-1015 Typical Performance

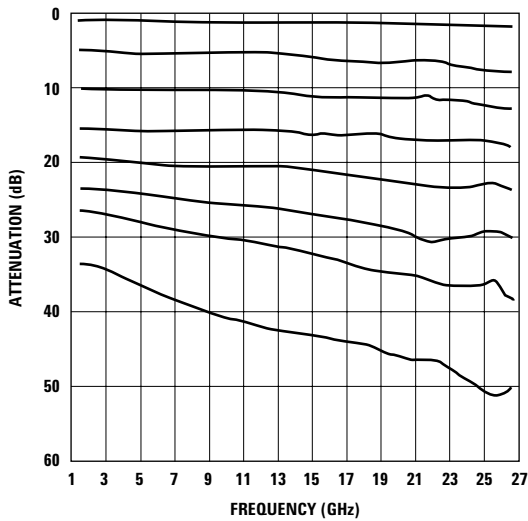


Figure 5. Attenuation vs. Frequency.^[1]

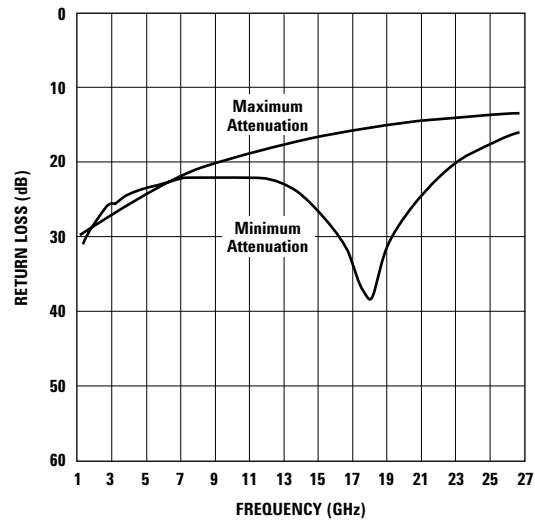


Figure 6. Output Return Loss vs. Frequency.^[1]

Note:

1. Data obtained from on-wafer measurements. $T_{\text{chuck}} = 25^{\circ}\text{C}$.

HMMC-1015 Typical Temperature Performance

All Attenuation Settings were done at 1 GHz.

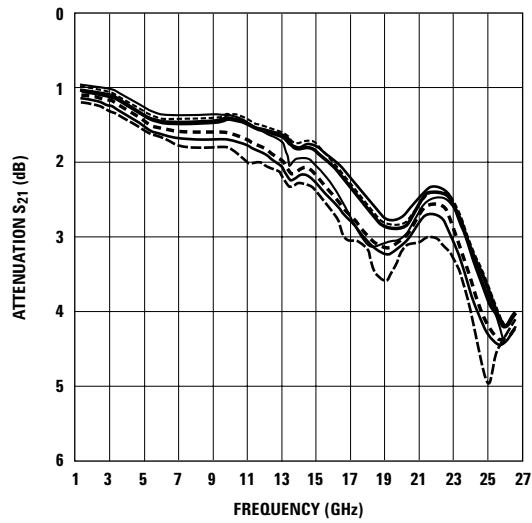


Figure 7. Attenuation vs. Temperature @ Minimum Attenuation.^[1]

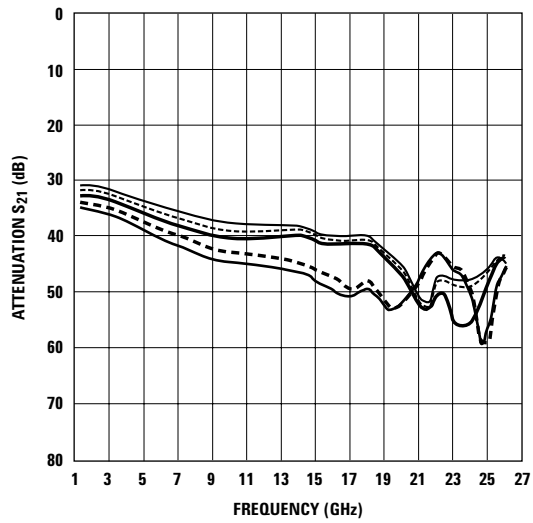


Figure 8. Attenuation vs. Temperature @ Maximum Attenuation.^[1]

Note:

1. Data taken with the device mounted in connectorized package.

Key for Temperature Settings:

- -55°C
- -25°C
- 0°C
- - - +25°C
- +55°C
- - - +85°C

This data sheet contains a variety of typical and guaranteed performance data. The information supplied should not be interpreted as a complete list of circuit specifications. In this data sheet the term *typical* refers to the 50th percentile performance. For additional information contact your local Agilent Technologies' sales representative.

www.semiconductor.agilent.com

Data subject to change.

Copyright © 2001 Agilent Technologies, Inc.

Obsoletes 5968-4446E

May 18, 2001

5988-2547EN



Agilent Technologies